

## FQPF3N25

# Power MOSFET, N-Channel, QFET®, 250 V, 2.3 A, 2.2 Ω, TO-220F

## Product Overview

For complete documentation, see the data sheet.

These N-Channel enhancement mode power field effect transistors are produced using ON Semiconductor's proprietary, planar stripe, DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switching DC/DC converters, switch mode power supply.

## Features

- 2.3 A, 250 V,  $R_{DS(on)} = 2.2 \Omega$  (Max.) @  $V_{GS} = 10 \text{ V}$ ,  $I_D = 1.15 \text{ A}$
- Low Gate Charge (Typ. 4.0 nC)
- Low  $C_{rss}$  (Typ. 4.7 pF)
- 100% Avalanche Tested

## Applications

- High Efficiency Switching DC/DC Converters
- Switched Mode Power Supplies

## Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	$V_{DSS}^{(BR)}$ Min (V)	$V_{GS}^{(h)}$ Max (V)	$V_{GS}^{(t)}$ Max (V)	$I_D$ Max (A)	$P_D$ Max (W)	$R_{DS(on)}^{(h)}$ Max @ $V_{GS} = 2.5 \text{ V}$ (mΩ)	$R_{DS(on)}^{(t)}$ Max @ $V_{GS} = 4.5 \text{ V}$ (mΩ)	$R_{DS(on)}^{(t)}$ Max @ $V_{GS} = 10 \text{ V}$ (mΩ)	$Q_g$ Typ @ $V_{GS} = 4.5 \text{ V}$ (nC)	$Q_g$ Typ @ $V_{GS} = 10 \text{ V}$ (nC)	$C_{iss}$ Typ (pF)	Package Type
FQPF3N25	0.4705		Active	N-Channel		250	5	5	2.3	27	-	-	2200	4	130	TO-220-3 Full Pak	